

handsets, radar, avionics, missiles, etc.

Product Description

PRODUCT SPECIFICATION

PE83339

Military Operating Temperature Range

3.0 GHz Integer-N PLL for Low Phase Noise Applications

Features

- 3.0 GHz operation
- ÷10/11 dual modulus prescaler
- Internal phase detector with charge pump
- Serial programmable
- Low power 23 mA at 3 V
- Ultra-low phase noise
- Available in 20-lead TSSOP

counters, phase detector and a charge pump as shown in Figure 1. Counter values are programmable through a three wire serial interface.

Peregrine's PE83339 is a high performance integer-N PLL

superior phase noise performance of the PE83339 makes

it ideal for rugged military environments including: radio

The PE83339 features a 10/11 dual modulus prescaler.

capable of frequency synthesis up to 3.0 GHz. The

Fabricated in Peregrine's patented UTSi[®] (Ultra Thin Silicon) CMOS technology, the PE83339, while optimized for stringent military environments, offers excellent RF performance together with the economy and integration of conventional CMOS.

Figure 1. Block Diagram

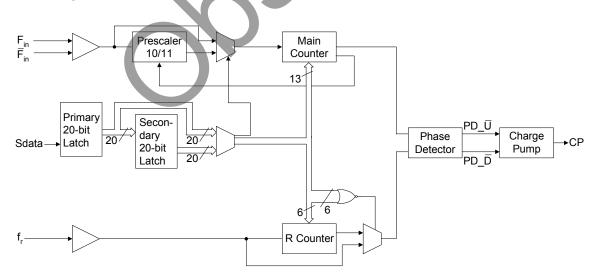




Figure 2. Pin Configuration

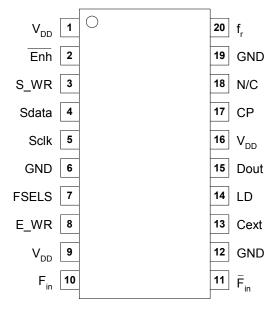


Table 1. Pin Descriptions

F _{in}	10		11 F _{in}
Table 1	. Pin Descr	iptions	
Pin No.	Pin Name	Туре	Description
1	V _{DD}	(Note 1)	Power supply input. Input may range from 2.85 V to 3.15 V. Bypassing required.
2	Enh	Input	Enhancement mode. When asserted low ("0"), enhancement register bits are functional. Internal 70 k Ω pull-up resistor.
3	S_WR	Input	Serial load enable input. While S_WR is "low", Sdata can be serially clocked. Primary register data are transferred to the secondary register on S_WR rising edge.
4	Sdata	Input	Binary serial data input. Input data entered MSB first.
5	Sclk	Input	Serial clock input. Sdata is clocked serially into the 20-bit primary register (E_WR "low") or the 8-bit enhancement register (E_WR "high") on the rising edge of Sclk.
6	GND		Ground.
7	FSELS	Input	Selects contents of primary register (FSELS=1) or secondary register (FSELS=0) for programming of internal counters. Internal 70 kΩ pull-down resistor.
8	E_WR	Input	Enhancement register write enable. While E_WR is "high", Sdata can be serially clocked into the enhancement register on the rising edge of Sclk. Internal 70 k Ω pull-down resistor.
9	V _{DD}	(Note 1)	Same as pin 1.
10	F _{in}	Input	Prescaler input from the VCO. Max frequency input is 3.0 GHz.
11	F _{in}	Input	Prescaler complementary input. A bypass capacitor should be placed as close as possible to this pin and be connected in series with a 50 Ω resistor to the ground plane.
12	GND		Ground.
13	Cext	Output	Logical "NAND" of PD_U and PD_D terminated through an on chip, 2 kΩ series resistor. Connecting Cext to an external capacitor will low pass filter the input to the inverting amplifier used for driving LD.
14	LD	Output, OD	Lock detect is an open drain logical inversion of CEXT. When the loop is in lock, LD is high impedance, otherwise LD is a logic low ("0").
15	Dout	Output	Data out function, Dout, enabled in enhancement mode.
16	V _{DD}	(Note 1)	Same as pin 1.



Pin No.	Pin Name	Туре	Description
17	СР	Output	Charge pump current is sourced when $f_{\rm c}$ leads $f_{\rm p}$ and sinked when $f_{\rm c}$ lags $f_{\rm p}.$
18	NC	Output	No connection.
19	GND		Ground.
20	f _r	Input	Reference frequency input.

Note 1: V_{DD} pins 1, 9, and 16 are connected by diodes and must be supplied with the same positive voltage level.

Table 2. Absolute Maximum Ratings

Symbol	Parameter/Conditions	Min	Max	Units
V _{DD}	Supply voltage	-0.3	4.0	V
Vı	Voltage on any input	-0.3	V _{DD} + 0.3	V
I,	DC into any input	-10	+10	mA
Ιo	DC into any output	-10	+10	mA
T _{stg}	Storage temperature range	-65	150	°C

Table 3. Operating Ratings

Symbol	Parameter/Conditions	Min	Max	Units
V _{DD}	Supply voltage	2.85	3.15	V
T _A	Operating ambient temperature range	-55	125	°C

Table 4. ESD Ratings

Symbol	Parameter/Conditions	Level	Units
V_{ESD}	ESD voltage human body model (Note 1)	1000	V

Note 1: Periodically sampled, not 100% tested. Tested per MIL-STD-883, M3015 C2

Electrostatic Discharge (ESD) Precautions

When handling this $UTSi^{\ \ensuremath{\mathbb{S}}\ }$ device, observe the same precautions that you would use with other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the rating specified in Table 4.

Latch-Up Avoidance

Unlike conventional CMOS devices, *UTSi* [®] CMOS devices are immune to latch-up.

Table 5. DC Characteristics

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V_{DD} = 3.0 V, -55° C \leq T_{A} \leq 125° C, unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Units
I _{DD}	Operational supply current;	V _{DD} = 2.85 to 3.15 V				
	Prescaler enabled			23	35	mA
Digital Inputs:	S_WR, Sdata, Sclk					
VIH	High level input voltage	V _{DD} = 2.85 to 3.15 V	$0.7 \text{ x } V_{\text{DD}}$			V
VIL	Low level input voltage	V_{DD} = 2.85 to 3.15 V			$0.3 \times V_{\text{DD}}$	V
I _{IH}	High level input current	V _{IH} = V _{DD} = 3.15 V			+1	μA
IIL	Low level input current	V _{IL} = 0, V _{DD} = 3.15 V	-1			μA
Digital Inputs:	Enh (contains a 70 k Ω pull-up resistor)					
V _{IH}	High level input voltage	V _{DD} = 2.85 to 3.15 V	0.7 x V _{DD}			V
VIL	Low level input voltage	V _{DD} = 2.85 to 3.15 V			$0.3 \times V_{DD}$	V
I _{IH}	High level input current	V _{IH} = V _{DD} = 3.15 V			+1	μA
IIL	Low level input current	V _{IL} = 0, V _{DD} = 3.15 V	-100			μA
Digital Inputs:	FSELS, E_WR (contains a 70 k Ω pull-down resi	stor)				
VIH	High level input voltage	V _{DD} = 2.85 to 3.15 V	0.7 x V _{DD}			V
VIL	Low level input voltage	V _{DD} = 2.85 to 3.15 V			0.3 x V _{DD}	V
I _{IH}	High level input current	V _{IH} = V _{DD} = 3.15 V			+100	μA
IIL	Low level input current	V _{IL} = 0, V _{DD} = 3.15 V	-1			μA
Reference Div	ider input: f _r					
I _{IHR}	High level input current	V _{IH} = V _{DD} = 3.15 V			+100	μA
I _{ILR}	Low level input current	V _{IL} = 0, V _{DD} = 3.15 V	-100			μA
Counter outpu	it: Dout				- L L	
V _{OLD}	Output voltage LOW	l _{out} = 6 mA			0.4	V
V _{OHD}	Output voltage HIGH	l _{out} = -3 mA	V _{DD} - 0.4			V
Lock detect of	utputs: (Cext, LD)					
V _{OLC}	Output voltage LOW, Cext	$I_{out} = 0.1 \text{ mA}$			0.4	V
V _{OHC}	Output voltage HIGH, Cext	I _{out} = -0.1 mA	V _{DD} - 0.4			V
V _{OLLD}	Output voltage LOW, LD	I _{out} = 1 mA			0.4	V
Charge Pump	output: CP					
I_{CP} – Source	Drive current	$V_{CP} = V_{DD} / 2$	-2.6	-2	-1.4	mA
I_{CP} – Sink	Drive current	$V_{CP} = V_{DD} / 2$	1.4	2	2.6	mA
I _{CPL}	Leakage current	$1.0 \text{ V} < \text{V}_{\text{CP}} < \text{V}_{\text{DD}} - 1.0 \text{ V}$	-1		1	μA
I _{CP} – Source vs. I _{CP} Sink	Sink vs. source mismatch	$V_{CP} = V_{DD} / 2$, $T_A = 25^{\circ} C$			15	%
I_{CP} vs. V_{CP}	Output current magnitude variation vs. voltage	1.0 V < V _{CP} < V _{DD} - 1.0 V T _A = 25° C			15	%

Table 6. AC Characteristics



V_{DD} = 3.0 V, -55° C \leq T_{A} \leq 125° C, unless otherwise specified

Symbol	Parameter	s Min	Max	Units	
Control Interfa	ace and Latches (see Figures 3, 4, 5)				
f _{Clk}	Serial data clock frequency	(Note 1)		10	MHz
t _{CIKH}	Serial clock HIGH time		30		ns
t _{CIkL}	Serial clock LOW time		30		ns
t _{DSU}	Sdata set-up time to Sclk rising edge		10		ns
t _{DHLD}	Sdata hold time after Sclk rising edge		10		ns
t _{PW}	S_WR pulse width		30		ns
t _{CWR}	Sclk rising edge to S_WR rising edge		30		ns
t _{CE}	Sclk falling edge to E_WR transition		30		ns
t _{WRC}	S_WR falling edge to Sclk rising edge		30		ns
t _{EC}	E_WR transition to Sclk rising edge		30		ns
Main Divider (Including Prescaler)	· · ·			•
Fin	Operating frequency		500	3000	MHz
P_{Fin}	Input level range	External AC coupling	-5	5	dBm
		(85°C < T _A ≤ 125°C)	0	5	MHz
		External AC coupling			
Main Divider (Prescaler Bypassed)				
Fin	Operating frequency		50	300	MHz
P _{Fin}	Input level range	External AC coupling	0	5	dBm
		External AC coupling	0	5	MHz
		85°C < T _A ≤ 125°C			
Reference Div	ider				
f _r	Operating frequency	(Note 3)		100	MHz
P _{fr}	Reference input power (Note 2)	Single ended input	0		dBm
Phase Detecto	pr				1
f _c	Comparison frequency	(Note 3)		20	MHz
SSB Phase No	bise : Output Referred (F _{in} = 1.3 GHz, f _r =	10 MHz, f _c = 1.25 MHz, LBW = 70 kHz)	I		
PNOR	Output Referred Phase Noise	100 Hz Offset: V _{DD} = 3.0V, T = 25°	С	-85	(Note 4)
PN _{OR}	Output Referred Phase Noise	1000 Hz Offset: V _{DD} = 3.0V, T = 25°		-93	(Note 4)

Note 1: fclk is verified during the functional pattern test. Serial programming sections of the functional pattern are clocked at 10 MHz to verify fclk specification.

Note 2: CMOS logic levels can be used to drive reference input if DC coupled. Voltage input needs to be a minimum of 0.5 Vp-p. For optimum phase noise performance, the reference input falling edge rate should be faster than 80mV/ns.

Note 3: Parameter is guaranteed through characterization only and is not tested.

Note 4: All devices are screened to phase noise limits listed in Table 7. The magnitude of the tester uncertainty precludes testing phase noise as part of qualification testing. These parameters are also exempt from PDA requirements.

Table 7. Phase Noise Test

Test name	Conditions	Max	Units
Phase Noise	100 Hz Offset	-73	dBc/Hz
	1000 Hz Offset	-83	dBc/Hz

Functional Description

The *PE83339* consists of a prescaler, counters, a phase detector, charge pump and control logic. The

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dual modulus prescaler divides the VCO frequency by either 10 or 11, depending on the value of the

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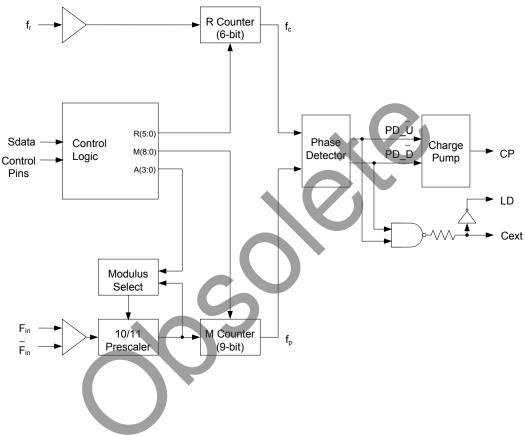


modulus select. Counters "R" and "M" divide the reference and prescaler output, respectively, by integer values stored in a 20-bit register. An additional counter ("A") is used in the modulus select logic.

The phase-frequency detector generates up and down frequency control signals which direct the

charge pump operation. The control logic includes a selectable chip interface. Data is written into the internal registers via the three wire serial bus. There are also various operational and test modes and a lock detect output.





Main Counter Chain

Normal Operating Mode

Setting the Pre_en control bit "low" enables the $\div 10/11$ prescaler. The main counter chain then divides the RF input frequency (F_{in}) by an integer derived from the values in the "M" and "A" counters.

In this mode, the output from the main counter chain (f_p) is related to the VCO frequency (F_{in}) by the following equation:

 $f_p = F_{in} / [10 \times (M+1) + A]$ (1) where $A \le M + 1, 1 \le M \le 511$

When the loop is locked, F_{in} is related to the reference frequency (f_r) by the following equation:

 $F_{in} = [10 \ x \ (M+1) + A] \ x \ (f_r / (R+1))$ (2) where $A \le M+1, \ 1 \le M \le 511$

A consequence of the upper limit on A is that F_{in} must be greater than or equal to 90 x (f_r / (R+1)) to obtain contiguous channels. The A counter can accept values as high as 15, but in typical operation it will cycle from 0 to 9 between increments in M.

Programming the M counter with the minimum allowed value of "1" will result in a minimum M counter divide ratio of "2".

Prescaler Bypass Mode

Setting the frequency control register bit Pre_en "high" allows F_{in} to bypass the $\pm 10/11$ prescaler. In this mode, the prescaler and A counter are powered down, and the input VCO frequency is divided by the M counter directly. The following equation relates F_{in} to the reference frequency f_r :

 $F_{in} = (M + 1) x (f_r / (R+1))$ where $1 \le M \le 511$ (3)

Reference Counter

The reference counter chain divides the reference frequency f_r down to the phase detector comparison frequency f_c .

The output frequency of the 6-bit R Counter is related to the reference frequency by the following equation:

 $f_c = f_r / (R + 1)$ where $0 \le R \le 63$ (4)

Note that programming R with "0" will pass the reference frequency (f_r) directly to the phase detector.

Register Programming

Serial Interface Mode

While the E_WR input is "low" and the S_WR input is "low", serial input data (Sdata input), B_0 to B_{19} , are clocked serially into the primary register on the rising edge of Sclk, MSB (B_0) first. The contents from the primary register are transferred into the secondary register on the rising edge of either S_WR according to the timing diagrams shown in Figure 4. Data are transferred to the counters as shown in Table 7 on page 9.

The double buffering provided by the primary and secondary registers allows for "ping-pong" counter control using the FSELS input. When FSELS is "high", the primary register contents set the counter inputs. When FSELS is "low", the secondary register contents are utilized.

While the E_WR input is "high" and the S_WR input is "low", serial input data (Sdata input), B_0 to B_7 , are clocked serially into the enhancement register on the rising edge of Sclk, MSB (B_0) first. The enhancement register is double buffered to prevent inadvertent control changes during serial loading, with buffer capture of the serially entered data performed on the falling edge of E_WR according to the timing diagram shown in Figure 4. After the falling edge of E_WR, the data provide control bits as shown in Table 8 on page 9 will have their bit functionality enabled by asserting the Enh input "low".





Table 8. Primary Register Programming

Interface Mode	Enh	R₅	R₄	M ₈	M ₇	Pre_en	M ₆	M₅	M₄	M ₃	M ₂	M₁	Mo	R ₃	R ₂	R ₁	R₀	A ₃	A ₂	A 1	A ₀
Serial*	1	B ₀	B ₁	B ₂	B ₃	B ₄	B ₅	B ₆	B ₇	B ₈	B ₉	B ₁₀	B ₁₁	B ₁₂	B ₁₃	B ₁₄	B ₁₅	B ₁₆	B ₁₇	B ₁₈	B ₁₉

*Serial data clocked serially on Sclk rising edge while E_WR "low" and captured in secondary register on S_WR rising edge.



(last in) LSB

Table 9. Enhancement Register Programming

Interface Mode	Enh	Reserved	Reserved	f _p Output	Power down	Counter Ioad	MSEL output	f _c output	Reserved
Serial*	0	B ₀	B ₁	B ₂	B ₃	B ₄	B ₅	B ₆	B ₇
Serial data cl		↑	g edge while E <u>.</u>	_WR "high" and	captured in the	e double buffer o	on E_WR falling	edge.	Ť
		MSB (first in)				×	0		(last in) LSB
igure 4. S	Serial Ir	nterface Mo	ode Timing	J Diagram		0			
Sdata		\times		\rightarrow					
				C	U			[
E_WR								$ \rightarrow $	
		×	t _{EC}	Y			4	t _{ce}	
Sclk									
									7
6_WR		t _{DSI}	. t	DHLD	+	ikh t _{CikL}		_{cwr} t _{pw}	
		*DSI			°0	IKH "ClkL		SWR PW	t _{wrc}



Enhancement Register

The functions of the enhancement register bits are shown below with all bits active "high".

Table 10.	Enhancement Register Bit Functionality
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Bit Function		Description
Bit 0	Reserved**	
Bit 1	Reserved**	
Bit 2	f _p output	Drives the M counter output onto the Dout output.
Bit 3	Power down	Power down of all functions except programming interface.
Bit 4	Counter load	Immediate and continuous load of counter programming.
Bit 5	MSEL output	Drives the internal dual modulus prescaler modulus select (MSEL) onto the Dout output.
Bit 6	f _c output	Drives the reference counter output onto the Dout output
Bit 7	Reserved**	

** Program to 0

Phase Detector

The phase detector is triggered by rising edges from the main Counter (f_p) and the reference counter (f_c). It has two outputs, namely PD_U, and PD_D. If the divided VCO leads the divided reference in phase or frequency (f_p leads f_c), PD_D pulses "low". If the divided reference leads the divided VCO in phase or frequency (f_c leads f_p), PD_U pulses "low". The width of either pulse is directly proportional to phase offset between the two input signals, f_p and f_c .

The signals from the phase detector couple directly to a charge pump. PD_U controls a current source at pin CP with constant amplitude and pulse duration approximately the same as PD_U. PD_D similarly drives a current sink at pin CP. The current pulses from pin CP are low pass filtered externally and then connected to the VCO tune voltage. PD_U pulses result in a current source, which increases the VCO frequency and PD_D results in a current sink, which decreases VCO frequency when using a positive Kv VCO.

A lock detect output, LD is also provided, via the pin Cext. Cext is the logical "NAND" of PD_U and PD_D waveforms, which is driven through a series 2 kohm resistor. Connecting Cext to an external shunt capacitor provides low pass filtering of this signal. Cext also drives the input of an internal inverting comparator with an open drain output. Thus LD is an "AND" function of PD_U and PD_D.

Figure 5. Typical PE83339 Loop Filter Application Example

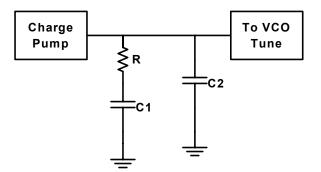




Figure 6. Package Drawing

20-lead TSSOP (JEDEC MO-153-AC)

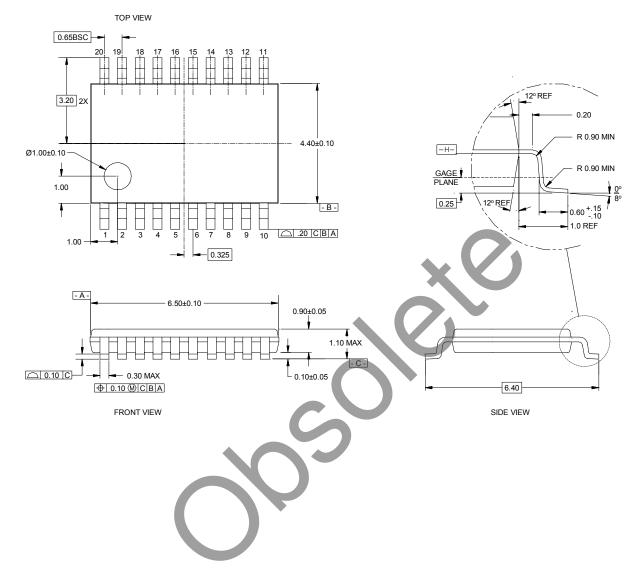


Table 11. Ordering Information

Order Code	Part Marking	Description	Package	Shipping Method
83339-11	PE83339	PE83339-20TSSOP-74A	20-lead TSSOP	74 units / Tube
83339-12	PE83339	PE83339-20TSSOP-200C	20-lead TSSOP	2000 units / T&R
83339-00	PE83339EK	PE83339-20TSSOP-EVAL KIT	20-lead TSSOP	1 / Box

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Data Sheet Identification

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